

SMD Type

MOSFET

MOS Field Effect Transistor

2SJ598

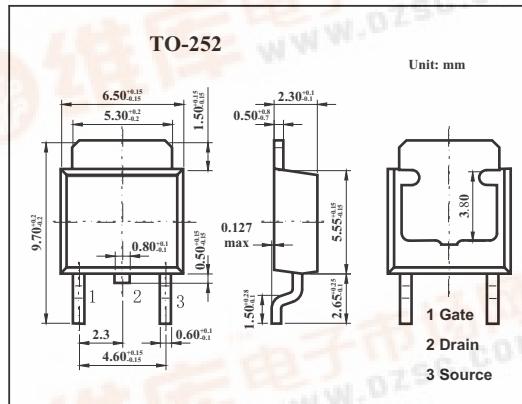
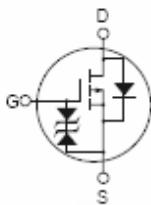
■ Features

- Low on-resistance

$R_{DS(on)1} = 130 \text{ m}\Omega \text{ MAX. } (V_{GS} = -10 \text{ V}, I_D = -6 \text{ A})$

$R_{DS(on)2} = 190 \text{ m}\Omega \text{ MAX. } (V_{GS} = -4.0 \text{ V}, I_D = -6 \text{ A})$

- Low Ciss: $C_{iss} = 720 \text{ pF TYP.}$
- Built-in gate protection diode



■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Rating	Unit
Drain to source voltage	V_{DSS}	-60	V
Gate to source voltage	V_{GSS}	± 20	V
Drain current (DC)	I_D	± 12	A
Drain current(pulse) *	I_D	± 30	A
Power dissipation	P_D	23	W
Channel temperature	T_{ch}	150	$^\circ\text{C}$
Storage temperature	T_{stg}	-55 to +150	$^\circ\text{C}$

* $PW \leq 10 \mu\text{s}$, duty cycle $\leq 1\%$

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■ Electrical Characteristics Ta = 25°C

Parameter	Symbol	Testconditons	Min	Typ	Max	Unit
Drain cut-off current	Idss	Vds=-60V,Vgs=0			-10	µ A
Gate leakage current	IGSS	Vgs=±16V,Vds=0			±10	µ A
Gate to source cutoff voltage	VGS(off)	Vds=-10V,Id=-1mA	-1.5	-2.0	-2.5	V
Forward transfer admittance	Yfs	Vds=-10V,Id=-6A	5	11		S
Drain to source on-state resistance	RDS(on)	Vgs=-10V,Id=-6A		102	130	mΩ
		Vgs=-4.0V,Id=-6A		131	190	mΩ
Input capacitance	Ciss	Vds=-10V,Vgs=0,f=1MHZ		720		pF
Output capacitance	Coss			150		pF
Reverse transfer capacitance	Crss			50		pF
Turn-on delay time	td(on)	VGS(on)=-10V,Id=-6A ,VDD=-30V,RG=0Ω		70		ns
Rise time	tr			4		ns
Turn-off delay time	td(off)			35		ns
Fall time	tf			10		ns
Total Gate Charge	QG	I _D = -12 A		15		nC
Gate to Source Charge	QGS	VDD= -48 V		3		nC
Gate to Drain Charge	QGD	VGS =-10 V		4		nC
Body Diode Forward Voltage	VF(S-D)	I _F = 12 A, V _{GS} = 0 V		0.98		V
Reverse Recovery Time	trr	I _F = 12 A, V _{GS} = 0 V di/dt = 100 A / µ s		50		ns
Reverse Recovery Charge	Qrr			100		nC